

a gate line of (n+1)-th row provided on said substrate;

a gate line of (n+2)-th row provided on said substrate;

a data line of m-th column provided on said substrate;

a pixel electrode of n-th row and m-th column provided on said substrate and connected with said data line and said gate line of n-th row through corresponding at least one transistor; said pixel electrode being superposed on said [data line] gate line of (n+1)-th row with an insulator therebetween and superposed on said gate line of n-th row with an insulator therebetween; and

a pixel electrode of (n+1)-th row and m-th column provided on said substrate and connected with said data line and said gate line of (n+1)-th row through corresponding at least one transistor, said pixel electrode of (n+1)-th row and m-th column being superposed on said [data line] gate line of (n+2)-th row with an insulator therebetween and superposed on said gate line of (n+1)-th row with an insulator therebetween,

wherein said pixel electrode of n-th row and m-th column is provided on an opposite side of said data line to said pixel electrode of (n+1)-th row and m-th column.

22. (twice amended) An electro-optical device of an active matrix comprising:

a first gate line provided on a substrate;

a second gate line provided adjacent to said first gate line on said substrate;

a first pixel electrode provided on said substrate and connected with said first gate line through at least one first transistor; and

a second pixel electrode provided on said substrate and connected with said second gate line through at least one second transistor,

wherein said first pixel electrode is superposed on said first gate line with an insulator therebetween and is superposed on said second gate line with another insulator therebetween and wherein a difference between [the] area shared by said first

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gate line and said first pixel electrode and area shared by said second gate line and said first pixel electrode is not more than one tenth of sum of said area shared by said first gate line and said first pixel electrode and said area shared by said second gate line and said first pixel electrode.

23. (amended) An electro-optical device of an active matrix comprising:

- a gate line provided on a substrate;
- a data line provided on said substrate;
- a wiring provided on said substrate;

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a pixel electrode provided on said substrate and superposed on said gate line with a first insulator therebetween and superposed on said wiring with a second insulator therebetween; and

at least one transistor provided on said substrate and connected with said gate line at a gate thereof and connected with said data line at one of source and drain thereof and connected with said pixel electrode at the other one of the source and drain,

[wherein said first insulator comprises an anodic oxide of a material of said gate line, and said second insulator comprises an anodic oxide of a material of said wiring]

wherein a capacitance comprising said gate line, said pixel electrode and said first insulator is provided intentionally.

Please add new claim 24 as follows:

--24. An electro-optical device of an active matrix comprising:

- a gate line provided on a substrate;
- a data line provided on said substrate;
- a wiring provided on said substrate;

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